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# The Effect of Local Structure and Non-uniformity on Decoherence-Free States of Charge Qubits

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We analyze robustness of decoherence-free (DF) subspace in charge qubits when there are a local structure and non-uniformity that violate collective decoherence measurement condition. We solve master equations of up to four charge qubits and a detector as two serially coupled quantum point contacts (QPC) with an island structure. We show that robustness of DF states is strongly affected by local structure as well as by non-uniformities of qubits.

## I. INTRODUCTION

Decoherence-free(DF) states[1] are useful for collective decoherence environment, even if there is a small symmetry breaking perturbation parameterized by $\eta$ in the order of O($\eta$) ($\eta \ll 1$)[2]. Nowadays, experiments for DF states have been successful up to four qubits in photon system[3] and in nuclear magnetic resonance (NMR)[4]. However, in solid-state qubits, it seems to be more difficult to realize the collective decoherence environment than in the case of optical or NMR qubits. This is because we could not prepare plenty of qubits with mathematically exact size, because the sizes of Cooper-pair box[5,6] or quantum dot (QD)[7,8,9,10] are less than hundreds of nm, and moreover, localized trap sites generated in the fabrication process disturb the collective decoherence environment.

We theoretically describe the effect of non-uniform environment on DF states of charge qubits composed of coupled QDs, considering the measurement process, by using time-dependent density matrix (DM) equations. The charge distribution of the qubits changes the QPC current capacitively, resulting in detection and corruption of charged state (backaction)[12]. Thus, measurement is a basic and important decoherence process that should be investigated in detail. In Ref.[13], we discussed the robustness of DF states under non-uniformity of qubits when they are detected by a simple structureless QPC detector. However, generally speaking, the solid-state qubit system is arranged compactly to avoid extra noises, and therefore, qubits have a tendency to be often affected by geometrical local structures such as electrodes or electrical wires. In addition, when there are local structures and large non-uniformities, it is possible that the four-qubit DF states are less robust than non-DF states. In such cases, for example, two qubit non-DF state and the singlet state would be appropriate to constitute two logical states instead of using four-qubit DF states, because defects and fault rates will increase as the number of qubits increases.

In this paper, we discuss the effect of local structures on the DF states combining with the non-uniformity of qubits based on the setup shown in Fig. 1(a) and compare them with two-qubit states shown in Fig. 1(b). We study

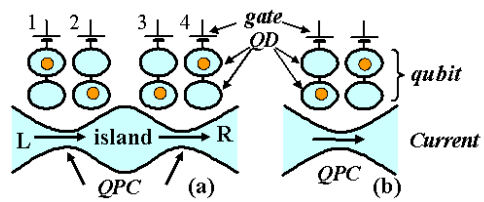


FIG. 1: Qubits that use double dot charged states are capacitively coupled to a QPC detector.

the robustness of four-qubit DF states written as:

$$\begin{aligned}
|\Psi_1^{[4]}\rangle_{(1234)} &= 2^{-1}(|01\rangle - |10\rangle)_{(12)} \otimes (|01\rangle - |10\rangle)_{(34)}, \\
|\Psi_2^{[4]}\rangle_{(1234)} &= 1/(2\sqrt{3})(2|0011\rangle - |0101\rangle - |0110\rangle \\
&- |1001\rangle - |1010\rangle + 2|1100\rangle)_{(1234)} \\
|\Psi_3^{[4]}\rangle_{(1234)} &= |\Psi_1^{[4]}\rangle_{(1432)} \qquad (1)
\end{aligned}$$

where $|1001\rangle_{(1234)} = |1\rangle_1|0\rangle_2|0\rangle_3|1\rangle_4$ and so on. We also compare these four-qubit DF states with two qubit Bell states: $|a\rangle \equiv (|\downarrow\downarrow\rangle + |\uparrow\uparrow\rangle)/\sqrt{2}$, $|b\rangle \equiv (|\downarrow\downarrow\rangle - |\uparrow\uparrow\rangle)/\sqrt{2}$, $|c\rangle \equiv (|\downarrow\uparrow\rangle + |\uparrow\downarrow\rangle)/\sqrt{2}$, $|d\rangle \equiv (|\downarrow\uparrow\rangle - |\uparrow\downarrow\rangle)/\sqrt{2}$ depicted in Fig. 1 (b).

## II. FORMULATION

We show the formulation for Fig. 1(a). The Hamiltonian for the combined qubits and the QPC for Fig. 1(a) is written as $H = H_{\rm qb} + H_{\rm qpc} + H_{\rm int}$. $H_{\rm qb}$ describes the interacting four qubits: $H_{\rm qb} = \sum_{i=1}^{N}(\Omega_i\sigma_{ix} + \epsilon_i\sigma_{iz}) + \sum_{i=1}^{N-1} J_{i,i+1}\sigma_{iz}\sigma_{i+1z}$, where $\Omega_i$ and $\epsilon_i$ are the inter-QD tunnel coupling and energy difference (gate bias) within each qubit. Here, spin operators are used instead of annihilation operators of an electron in each qubit. $J_{i,i+1}$ is a coupling constant between two nearest qubits, originating from capacitive couplings in the QD system[11]. $|\uparrow\rangle$ and $|\downarrow\rangle$ refer to the two single-qubit states in which the excess charge is localized in the upper and lower dot, respectively.

The two serially coupled QPCs are described by

$$H_{\rm qpc} = \sum_{\substack{\alpha=L,R \\ s=\uparrow,\downarrow}} \sum_{i_\alpha} \Big[ E_{i_\alpha} c^\dagger_{i_\alpha s} c_{i_\alpha s} + V_{i_\alpha s}(c^\dagger_{i_\alpha s} d_s + d^\dagger_s c_{i_\alpha s}) \Big]$$

$$+ \sum_{s=\uparrow,\downarrow} E_d d_s^\dagger d_s + U d_\uparrow^\dagger d_\uparrow d_\downarrow^\dagger d_\downarrow \,. \quad (2)$$

Here, $c_{i_L s}(c_{i_R s})$ is the annihilation operator of an electron in the $i_L$th ($i_R$th) level ($i_L(i_R) = 1, ..., n$) of the left (right) electrode, $d_s$ is the electron annihilation operator of the island between the QPCs, $E_{i_L s}(E_{i_R s})$ is the energy level of electrons in the left (right) electrode, and $E_d$ is that of the island. Here, we assume only one energy level on the island between the two QPCs, with spin degeneracy. $V_{i_L s}$ ($V_{i_R s}$) is the tunneling strength of electrons between the left (right) electrode state $i_L s$ ($i_R s$) and the island state. $U$ is the on-site Coulomb energy of double occupancy in the island.

$H_{\rm int}$ is the capacitive interaction between the qubits and the QPC, that induces *dephasing* between different eigenstates of $\sigma_{iz}$[1]. Most importantly, it takes into account the fact that localized charge near the QPC increases the energy of the system electrostatically, thus affecting the tunnel coupling between the left and right electrodes:

$$\begin{aligned} H_{\rm int} &= \sum_{i_L,s} \left[ \sum_{i=1}^{2} \delta V_{i_L,is} \sigma_{iz} \right] (c_{i_L s}^\dagger d_s + d_s^\dagger c_{i_L s}) \\ &+ \sum_{i_R,s} \left[ \sum_{i=3}^{4} \delta V_{i_R,is} \sigma_{iz} \right] (c_{i_R s}^\dagger d_s + d_s^\dagger c_{i_R s}) \quad (3) \end{aligned}$$

where $\delta V_{i_\alpha is}$ ($\alpha = L, R$) is an effective change of the tunneling strength between the electrodes and QPC island. Hereafter we neglect the spin dependence of $V_{i_\alpha}$ and $\delta V_{i_\alpha,i}$. We assume that the tunneling strength of electrons weakly depends on the energy $V_{i_\alpha i} = V_{i\alpha}(E_{i_\alpha})$ and electrodes are degenerate up to the Fermi surface $\mu_\alpha$. Then qubit states influence the QPC tunneling rate $\Gamma_L$ and $\Gamma_R$ by $\Gamma_L^{-1} = \Gamma_1^{-1} + \Gamma_2^{-1}$ and $\Gamma_R^{-1} = \Gamma_3^{-1} + \Gamma_4^{-1}$ through $\Gamma_i^{(\pm)} \equiv 2\pi\wp_\alpha(\mu_\alpha)|V_{i\alpha}^{(\pm)}(\mu_\alpha)|^2$ and $\Gamma_i^{(\pm)'} \equiv 2\pi\wp_\alpha(\mu_\alpha + U)|V_{i\alpha}^{(\pm)}(\mu_\alpha + U)|^2$, depending on the qubit state $\sigma_{iz} = \pm 1$ ($V_{i\alpha}^{(\pm)}(\mu_\alpha) = V_{i\alpha}(\mu_\alpha) \pm \delta V_{i\alpha}(\mu_\alpha)$ and $\wp_\alpha(\mu_\alpha)$ is the density of states of the electrodes ($\alpha = L, R$)). The values of $\Gamma_i^{(\pm)}$s are determined by the geometrical structure of the system. The strength of measurement is parameterized by $\Delta\Gamma_i$ as $\Gamma_i^{(\pm)} = \Gamma_{i0} \pm \Delta\Gamma_i$. The measurement strength $\zeta$ is related to the tunneling rates as $\Gamma_i = \Gamma_0(1 \pm \zeta)$ ($\Gamma_0$ is an unit)[13]. We call $|\downarrow\downarrow\rangle$, $|\downarrow\uparrow\rangle$, $|\uparrow\downarrow\rangle$, and $|\uparrow\uparrow\rangle$ $|A\rangle \sim |D\rangle$ respectively, and four-qubit states are written as $|AA\rangle$, $|AB\rangle$, ..,$|DD\rangle$. For uniform two qubits, $\Gamma_A = \Gamma_0(1-\zeta)/2$, $\Gamma_B = \Gamma_C = \Gamma_0(1-\zeta^2)/2$ and $\Gamma_D = \Gamma_0(1+\zeta)/2$ with $\zeta \equiv \Delta\Gamma/\Gamma_0$.

The DM equations of four qubits and detector at zero temperature of Fig. 1(a) are derived as in Ref.[13] by

$$\begin{aligned} \frac{d\rho_{z_1 z_2}^a}{dt} &= (i[J_{z_2} - J_{z_1}] - [\Gamma_L^{z_1} + \Gamma_L^{z_2}])\rho_{z_1 z_2}^a \\ &- i\sum_{j=1}^{N} \Omega_j (\rho_{g_j(z_1),z_2}^a - \rho_{z_1,g_j(z_2)}^a) + \sqrt{\Gamma_R^{z_1}\Gamma_R^{z_2}}(\rho_{z_1 z_2}^{b\uparrow} + \rho_{z_1 z_2}^{b\downarrow}), \end{aligned}$$

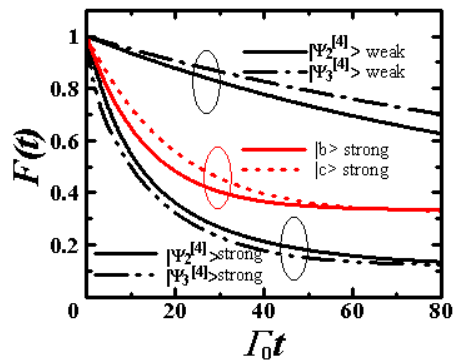


FIG. 2: Time-dependent fidelity of four-qubit states ($|\Psi_2^{[4]}\rangle$ and $|\Psi_3^{[4]}\rangle$) and two-qubit non-DF states ($|b\rangle$ and $|c\rangle$). The 'weak' means a weak measurement case of $\zeta = 0.2$ and the 'strong' means a strong measurement case of $\zeta = 0.6$. $\Omega = 2\Gamma_0$, $J_{ij} = 0$ $\epsilon_i = 0$. $\Gamma_i' = \Gamma_i$.

$$\begin{aligned} \frac{d\rho_{z_1 z_2}^{b_s}}{dt} &= \left( i[J_{z_2} - J_{z_1}] - \frac{\Gamma_L^{z_1'} + \Gamma_L^{z_2'} + \Gamma_R^{z_1} + \Gamma_R^{z_2}}{2} \right) \rho_{z_1 z_2}^{b_s} \\ &- i\sum_{j=1}^{N} \Omega_j (\rho_{g_r(z_1),z_2}^{b_s} - \rho_{z_1,g_r(z_2)}^{b_s}) + \sqrt{\Gamma_L^{z_1}\Gamma_L^{z_2}}\rho_{z_1 z_2}^a + \sqrt{\Gamma_R^{z_1'}\Gamma_R^{z_2'}}\rho_{z_1 z_2}^c, \\ \frac{d\rho_{z_1 z_2}^c}{dt} &= (i[J_{z_2} - J_{z_1}] - [\Gamma_R^{z_1'} + \Gamma_R^{z_2'}])\rho_{z_1 z_2}^c \\ &- i\sum_{j=1}^{N} \Omega_j (\rho_{g_r(z_1),z_2}^c - \rho_{z_1,g_r(z_2)}^c) + \sqrt{\Gamma_L^{z_1'}\Gamma_L^{z_2'}}(\rho_{z_1 z_2}^{b\uparrow} + \rho_{z_1 z_2}^{b\downarrow}), \end{aligned} \quad (4)$$

where $z_1, z_2 = AA, AB, ..., DD$ and, $\rho_{z_1 z_2}^a$, $\rho_{z_1 z_2}^{b_s}$ and $\rho_{z_1 z_2}^c$ are density matrix elements when no electron, one electron and two electrons exist in the QPC island, respectively. $J_{AA} = \sum_i^4 \epsilon_i + J_{12} + J_{23}$, $J_{AB} = \sum_i^3 \epsilon_i - \epsilon_4 + J_{12} - J_{23}$, ..., $J_{DD} = -\sum_i^4 \epsilon_i + J_{12} + J_{23}$. $g_l(z_i)$ and $g_r(z_i)$ are introduced for the sake of notational convenience and determined by the relative positions between qubit states as in Ref.[13]. We have 768 equations for four-qubits.

To see the decoherence effect explicitly, we study time-dependent *fidelity*, $F(t) \equiv {\rm Tr}[\rho(0)\rho'(t)]$ on the rotating coordinate as $\hat{\rho}'(t) = e^{i\sum \Omega_i' \sigma_{ix} t}\hat{\rho}(t)e^{-i\sum \Omega_i' \sigma_{ix} t}$ ($\Omega_i' \equiv \sqrt{\Omega_i^2 + \epsilon_i^2/4}$) to eliminate the bonding-antibonding coherent oscillations of free qubits (trace is carried out over qubit states).

## III. NUMERICAL RESULTS

Figure 2 shows the effect of the local structure, that is, an island in the QPC detector, on the fidelity of DF states. It is seen that the local structure greatly degrades the fidelity of qubit states. In particular, the degradation is large when the strength of measurement increases. Figure 2 also shows that non-DF two-qubit states are better than four qubit DF states when the strength of measurement is large. This result can be understood if we con-

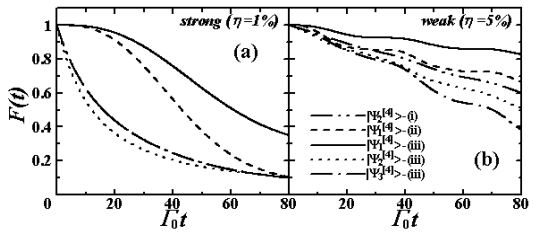


FIG. 3: Time-dependent fidelity of four-qubit DF states ($|\Psi_1^{[4]}\rangle$, $|\Psi_2^{[4]}\rangle$ and $|\Psi_3^{[4]}\rangle$) under various fluctuations : (i)$\Omega_3 = (1-\eta)\Omega$, $\epsilon_3 = \eta\Gamma_0$ and $\Gamma_3^{(\pm)} = (1-\eta)\Gamma^{(\pm)}$. (ii)$\Omega_2 = \Omega_3 = (1-\eta)\Omega$, $\epsilon_2 = \epsilon_3 = \eta\Gamma_0$ and $\Gamma_2^{(\pm)} = \Gamma_3^{(\pm)} = (1-\eta)\Gamma^{(\pm)}$. (iii)$\Omega_4 = (1-\eta)\Omega$, $\epsilon_4 = \eta\Gamma_0$ and $\Gamma_4^{(\pm)} = (1-\eta)\Gamma^{(\pm)}$. (a) $\eta$=0.01 and $\zeta$=0.6 (strong measurement), (b) $\eta$=0.05 and $\zeta$=0.2 (weak measurement). $\Omega = 2\Gamma_0$, $J_{ij} = 0$ $\epsilon_i = 0$. $\Gamma_i' = \Gamma_i$.

sider that the DF states that include many qubits have a disadvantage in that they are sensitive to local structures around them because they are distributed widely. In Ref[13], we showed that $|b\rangle$ state is a candidate of logical state in the weak measurement case, and $|c\rangle$ is a candidate in the strong measurement case, by exactly solving the DM equations analytically. Figure 2 supports the view that $|c\rangle$ state is better in the strong measurement case.

Figure 3 shows the combined effect of local QPC island structure and the non-uniformities of the qubits. In case (i), only 3rd qubit fluctuates as $\Omega_3 \to \Omega_3(1-\eta)$, $\epsilon_3 \to \epsilon_3(1-\eta)$ and $\Gamma_3 \to \Gamma_3(1-\eta)$. In case (ii), the 2nd and 3rd qubits fluctuate. In case (iii) only 4th qubit fluctuates. All of these non-uniformities are introduced in a manner similar to that described in Ref.[13].

Figure 3 (a) shows that non-uniformity of qubit does not change fidelity of $|\Psi_2^{[4]}\rangle$ and $|\Psi_3^{[4]}\rangle$ in the strong measurement case, when compared with Fig. 2. This is because the local structure has already greatly degraded the fidelity without non-uniformity as shown in Fig. 2. On the other hand, $|\Psi_1^{[4]}\rangle$, which is a product state of two singlet states, degrades due to the non-uniformity. Thus, the combination of local structure and non-uniformity degrades the four-qubit states even when the non-uniformity is small (1%).

Figure 3 (b) shows the robustness of four-qubit DF states depends on the distribution of non-uniformities in the qubits. Similar to the results in Ref.[13], the fidelities of case (iii) in $|\Psi_2^{[4]}\rangle$ and $|\Psi_3^{[4]}\rangle$ are smaller than those of other distributions of non-uniformities. For $|\Psi_1^{[4]}\rangle$, the distribution of case (ii) is the largest, because both the two singlets $2^{-1}(|01\rangle - |10\rangle)_{(12)}$ and $(|01\rangle - |10\rangle)_{(34)}$ are affected in the configuration of non-uniformity.

Figures 4 (a) and (b) show the fidelities for four-qubit DF states as a function of non-uniformity $\eta$ at $\Gamma_0 t = 50$. Basically, as $\eta$ increases, the fidelity decreases and the degradation strongly depends on the distribution of non-uniformity. Moreover, finite bias $\epsilon$ (*pure dephasing* region) reduces the fidelity more than in the zero bias cases. Figure 4 (b) can be compared with the Fig. 3 in Ref.[13] where QPC detector has no island structure: fidelity of the present island QPC detector is less than that of the structureless QPC in Ref.[13]. In particular, even at $\eta = 0$, fidelity in the present case degrades because the island in the QPC detector violates the collective decoherence environment.

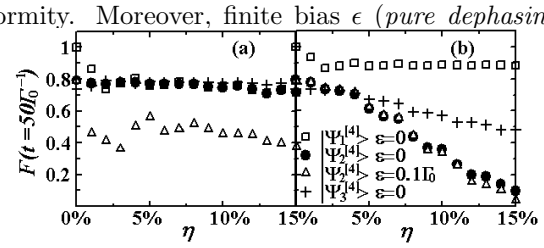


FIG. 4: Fidelities of four-qubit DF states at $t = 50\Gamma_0^{-1}$ as a function of non-uniformity $\eta$. (a) Non-uniformity for 2nd and 3rd qubits (case (ii)). (b) Non-uniformity for 4th qubit (case (iii)). $\Omega = 2\Gamma_0$, $J_{ij} = 0$ and $\zeta$=0.2.

## IV. CONCLUSION

We have solved master equations of four and two qubits with QPC detector, and discuss the robustness of DF states when there are a local structure and non-uniformities. We found that local structure is an obstacle to using DF states other than non-uniformities. We also showed that two-qubit non-DF states are candidates for the logical qubits even when there is some local structure.


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